

TSMC-03-065

March 9, 2004

To: Commissioner for Patents
P.O.Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject: | Serial No. 10/688,045 10/17/03 |

Huan-Just Lin et al.

FULLY DRY, Si RECESS FREE PROCESS FOR
REMOVING HIGH K DIELECTRIC LAYER

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
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P.O. Box 1450, Alexandria, VA 22313-1450, on March 16, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

Step B Ackerman 3/16/04

TSMC-03-065

Co-pending U.S. Patent Application TSMC-02-405, Serial No. 10/766,596, filed 01/27/04, assigned to the same assignee, "Zirconium Oxide and Hafnium Oxide Etching Using Halogen Containing Chemicals," discloses a method of selectively removing a high k dielectric layer from a substrate.

Sincerely,

A handwritten signature in black ink, appearing to read 'S. B. Ackerman', with a large, stylized loop at the end.

Stephen B. Ackerman,
Reg. No. 37761

(Use several sheets if necessary)

Application Number

10/688,045

Huan-Just Lin et al.

10/17/03

Group Art Unit

EXAMINER
M.D.A.

DOCUMENT NUMBER

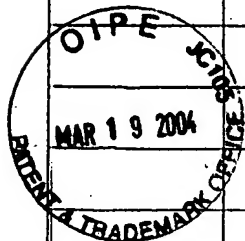
DATE

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DOCUMENT NUMBER

DATE

COUNTRY

CLASS

SUBCLASS

Translation

YES

NO

Co-pending U.S. Patent App. TSMC-02-405,
Serial No. 10/7166,596, filed 01/27/04, assigned
to the same assignee, "Zirconium Oxide and
Hafnium Oxide Etching Using Halogen Containing
Chemicals."

DATE CONTROLLED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.